

# United States Patent and Trademark Office



UNITED STATES DEPARTMENT OF COMMERCE United States Patent and Trademark Office Address: COMMISSIONER FOR PATENTS P.O. Box 1450 Alexandria, Virginia 22313-1450 www.uspto.gov

APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
10/717,904 11/21/2003		Minoru Niigaki	046124-5253	7368
55694 75	90 06/30/2006	EXAMINER		
DRINKER BIDDLE & REATH (DC)			GABOR, OTILIA	
1500 K STREET, N.W. SUITE 1100			ART UNIT	PAPER NUMBER
WASHINGTO	WASHINGTON, DC 20005-1209			

DATE MAILED: 06/30/2006

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)
	10/717,904	NIIGAKI ET AL.
Office Action Summary	Examiner	Art Unit
	Otilia Gabor	2884
The MAILING DATE of this communication appeared for Reply	ppears on the cover sheet with the	correspondence address
A SHORTENED STATUTORY PERIOD FOR REP WHICHEVER IS LONGER, FROM THE MAILING  - Extensions of time may be available under the provisions of 37 CFR 1 after SIX (6) MONTHS from the mailing date of this communication.  - If NO period for reply is specified above, the maximum statutory perior  - Failure to reply within the set or extended period for reply will, by state Any reply received by the Office later than three months after the mail earned patent term adjustment. See 37 CFR 1.704(b).	DATE OF THIS COMMUNICATIO 1.136(a). In no event, however, may a reply be tied and will apply and will expire SIX (6) MONTHS from the cause the application to become ABANDONE	N. mely filed the mailing date of this communication. ED (35 U.S.C. § 133).
Status		
1) ■ Responsive to communication(s) filed on 28 2a) ■ This action is FINAL. 2b) ■ The 3) ■ Since this application is in condition for allow closed in accordance with the practice under	nis action is non-final.  vance except for formal matters, pr	
Disposition of Claims		
4) ☐ Claim(s) 1-4 is/are pending in the application 4a) Of the above claim(s) is/are withdr 5) ☐ Claim(s) is/are allowed. 6) ☐ Claim(s) 1-4 is/are rejected. 7) ☐ Claim(s) is/are objected to. 8) ☐ Claim(s) are subject to restriction and	rawn from consideration.	
Application Papers		
9) ☐ The specification is objected to by the Examin 10) ☑ The drawing(s) filed on 21 November 2003 is Applicant may not request that any objection to the Replacement drawing sheet(s) including the correction. The oath or declaration is objected to by the	s/are: a)⊠ accepted or b)⊡ object ne drawing(s) be held in abeyance. Se ection is required if the drawing(s) is ob	ee 37 CFR 1.85(a). ojected to. See 37 CFR 1.121(d).
Priority under 35 U.S.C. § 119		
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of:  1. Certified copies of the priority docume 2. Certified copies of the priority docume 3. Copies of the certified copies of the priority docume application from the International Bure * See the attached detailed Office action for a list	ents have been received. ents have been received in Applicationity documents have been received in PCT Rule 17.2(a)).	tion No ed in this National Stage
Attachment(s)		
<ol> <li>Notice of References Cited (PTO-892)</li> <li>Notice of Draftsperson's Patent Drawing Review (PTO-948)</li> <li>Information Disclosure Statement(s) (PTO-1449 or PTO/SB/0 Paper No(s)/Mail Date</li> </ol>	4) Interview Summary Paper No(s)/Mail D  5) Notice of Informal 6) Other:	

Art Unit: 2884

### Response to Amendment

1. The amendment filed 04/28/2006 has been entered.

### Claim Rejections - 35 USC § 112

2. The following is a quotation of the first paragraph of 35 U.S.C. 112:

The specification shall contain a written description of the invention, and of the manner and process of making and using it, in such full, clear, concise, and exact terms as to enable any person skilled in the art to which it pertains, or with which it is most nearly connected, to make and use the same and shall set forth the best mode contemplated by the inventor of carrying out his invention.

3. Claims 1-4 are rejected under 35 U.S.C. 112, first paragraph, as failing to comply with the written description requirement. The claim(s) contains subject matter which was not described in the specification in such a way as to reasonably convey to one skilled in the relevant art that the inventor(s), at the time the application was filed, had possession of the claimed invention. The newly included subject matter that "each energy gap of said n-type nitride semiconductor layer and p-type nitride semiconductor layer is equal to or larger than the energy gap of said photoabsorption layer" constitutes new matter because the disclosure of the specification fails to include any relationship between the energy gap of the semiconductor layers and the energy gap of the photoabsorption layer. If the inventor is relying on the specification as quoted from page 1, line 23 to page 3, line 3 tO supply the missing description, which only discloses the semiconductor and photoabsorption layer materials and the transmittance of the selective wavelengths, which is nothing more than what was and is claimed in claims 1,

Art Unit: 2884

3 and 4, then the prior art (Kozodoy and Starikov) that was used to reject those claims also disclose this limitation.

### Claim Rejections - 35 USC § 103

- 4. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 5. This application currently names joint inventors. In considering patentability of the claims under 35 U.S.C. 103(a), the examiner presumes that the subject matter of the various claims was commonly owned at the time any inventions covered therein were made absent any evidence to the contrary. Applicant is advised of the obligation under 37 CFR 1.56 to point out the inventor and invention dates of each claim that was not commonly owned at the time a later invention was made in order for the examiner to consider the applicability of 35 U.S.C. 103(c) and potential 35 U.S.C. 102(e), (f) or (g) prior art under 35 U.S.C. 103(a).
- 6. Claims 1-4 are rejected under 35 U.S.C. 103(a) as being unpatentable over Kosodoy (6,265,727) or Starikov (6,608,360).

Kozodoy discloses a UV sensor system (detects wavelength less then 300 nm), the system comprising: an incident light window (52) constituting part of the container wall (51); a p-i-n – type photodiode disposed inside the container (51) and employed for photoelectrically converting the light (56) that was transmitted through the light window

Art Unit: 2884

(52); where the incident light window is made of glass and the photodiode comprises a photoabsorption layer (i-layer) formed from In<sub>y</sub>Ga<sub>(1-y)</sub>N (see Col.4, lines 18-31 where when x=0, Al is not present in the formula and therefore the only remaining elements are In, Ga and N in the above presented ratios), where 0≤y≤1; and the photoabsorption layer is positioned between an n-type nitride semiconductor layer (n-type GaN layer) and a p-type nitride semiconductor layer (p-type GaN layer). See Figs.1 and 5 and corresponding descriptions. Kozodoy also discloses that the energy gap of the active region is at least equal to one or both of the n or p-type regions.

Regarding claim 4 Kozodoy discloses that the detector is sensitive to wavelengths less than 300 nm and therefore (inherently) it's sensitivity is the same (so not more than 1/100) for both 365 and 405 nm.

Starikov discloses a UV sensor comprising: an incident light window (12) made of glass through which the incident light enters the detector and hits a p-i-n- type photodiode formed of a photoabsorption layer made of In<sub>x</sub>Ga<sub>(1-x)</sub>N (42) (where 0<x<0.2) and positioned between an n-type nitride semiconductor layer (40) and a p-type nitride semiconductor layer (44). Starikov discloses that the thickness and composition of these layers can be modified according to the desired wavelength sensitivity (one embodiment allows for same sensitivity in the 345-600 nm range). See figs. 1-4, 7 and corresponding descriptions.

Regarding claims 1 and 2 neither Kozodoy nor Starikov specifically disclose a borosilicate window with a thickness of 200 nm or more, however since none put a limit as to the type of glass to be used and the window thickness it would have been obvious

Art Unit: 2884

to use borosilicate glass and to use the claimed thickness since the modification would have involved a mere change in the size of a component which has been held to be within the level of ordinary skill in the art (*In re Rose*, 105 USPQ 237 (CCPA 1955)), and since it has been held that where the general conditions of a claim are disclosed in the prior art, discovering the optimum or workable ranges involves only routine skill in the art (*In re Aller*, 105 USPQ 233), and because using a readily available material for its suitability involves only routine skill in the art.

## Response to Arguments

7. Applicant's arguments filed 04/28/2006 have been fully considered but they are not persuasive. The main argument presented by the Applicant is that the newly introduced limitation that relates the energy gaps of the n and p-type semiconductor layers and the energy gap of the photoabsorption layer is not present in Kozodoy. This argument, however is not persuasive because 1) it fails under the 35 USC 112 for it represents new matter which is not supported by the specification (see rejection above) and 2) Kozodoy does disclose (as admitted in the response on page 12) that the energy gap of the active region (photoabsorption region) is of one or both of the n-type or p-type regions, which means that the energy gap of the photabsorption region is at least equal to the energy gap of the n-type and p-type semiconductor regions, which is what the claim asks for, and 3) Starikov clearly discloses this limitation (as admitted by Applicant on page 13 of the response).

Art Unit: 2884

#### Conclusion .

8. Applicant's amendment necessitated the new ground(s) of rejection presented in this Office action. Accordingly, **THIS ACTION IS MADE FINAL**. See MPEP § 706.07(a). Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period will expire on the date the advisory action is mailed, and any extension fee pursuant to 37 CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event, however, will the statutory period for reply expire later than SIX MONTHS from the date of this final action.

9. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Otilia Gabor whose telephone number is 571-272-2435. The examiner can normally be reached on Monday-Friday between 9am-5pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, David Porta can be reached on 571-272-2444. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Application/Control Number: 10/717,904

Art Unit: 2884

Page 7

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Otilia Gabor

**Primary Examiner** 

Art Unit 2884

OTILIA GABOR PRIMARY EXAMINER